

N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A) ^a	Q _g (TYP.)
20	0.0055 at V _{GS} = 4.5V	58	9.4 nC
	0.0057 at V _{GS} = 2.5 V	45	

FEATURES

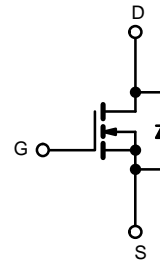
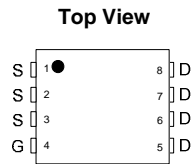
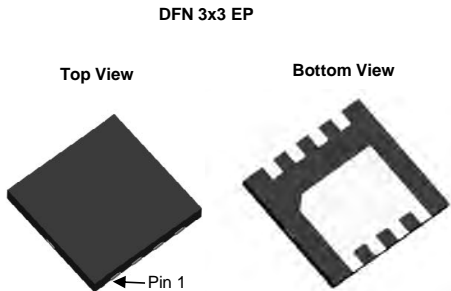
- TrenchFET® power MOSFET
- 100 % R_g and UIS tested

APPLICATIONS

- High power density DC/DC
- Synchronous rectification
- Embedded DC/DC



RoHS
COMPLIANT
HALOGEN
FREE



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V _{DS}	20	V	
Gate-Source Voltage	V _{GS}	+12		
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	58	A	
	T _C = 70 °C	46		
	T _A = 25 °C	19.8 ^{b, c}		
	T _A = 70 °C	15.8 ^{b, c}		
Pulsed Drain Current (t = 300 μs)	I _{DM}	150		
Continuous Source-Drain Diode Current	T _C = 25 °C	14.1		
	T _A = 25 °C	3.2 ^{b, c}		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	15	
Single Pulse Avalanche Energy		E _{AS}	11.25	mJ
Maximum Power Dissipation	T _C = 25 °C	P _D	31.2	W
	T _C = 70 °C		20	
	T _A = 25 °C		3.6 ^{b, c}	
	T _A = 70 °C		2.3 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150	°C	
Soldering Recommendations (Peak Temperature) ^{d, e}		260		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient ^{b, f}	t ≤ 10 s	R _{thJA}	24	34	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	3	4	

Notes

- Based on T_C = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- The DFN3X3 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: Manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 70 °C/W.

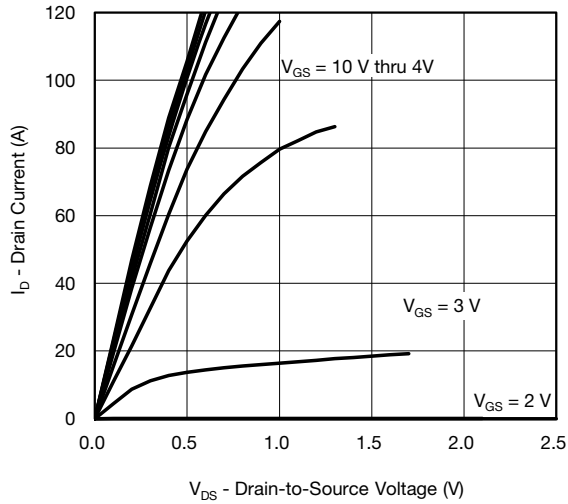
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	20	-	-	V
Drain-Source Breakdown Voltage (transient) ^c	$V_{DS(t)}$	$V_{GS} = 0\text{ V}, I_{D(aval)} = 15\text{ A}, t_{\text{transient}} = 50\text{ ns}$	26	-	-	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$	-	20	-	mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		-	-4.6	-	$^\circ\text{C}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.5	-	1.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 12\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	-	-	10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	30	-	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$	-	0.0055	-	Ω
		$V_{GS} = 2.5\text{ V}, I_D = 8\text{ A}$	-	0.0057	-	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 10\text{ A}$	-	65	-	S
Dynamic ^b						
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	1450	-	pF
Output Capacitance	C_{oss}		-	445	-	
Reverse Transfer Capacitance	C_{rss}		-	38	-	
C_{rss}/C_{iss} Ratio			-	0.026	0.052	
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	-	19.4	29	nC
Gate-Source Charge	Q_{gs}	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$	-	9.4	14	
Gate-Drain Charge	Q_{gd}		-	4	-	
Output Charge	Q_{oss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}$	-	1.8	-	
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.4	1.65	3.3	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$	-	9	18	ns
Rise Time	t_r		-	8	16	
Turn-Off Delay Time	$t_{d(off)}$		-	18	36	
Fall Time	t_f		-	8	16	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$	-	15	30	
Rise Time	t_r		-	12	24	
Turn-Off Delay Time	$t_{d(off)}$		-	18	36	
Fall Time	t_f		-	9	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$	-	-	14.1	A
Pulse Diode Forward Current ^a	I_{SM}		-	-	80	
Body Diode Voltage	V_{SD}	$I_S = 3\text{ A}$	-	0.76	1.1	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s},$ $T_J = 25\text{ }^\circ\text{C}$	-	24	48	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	14	28	nC
Reverse Recovery Fall Time	t_a		-	12	-	ns
Reverse Recovery Rise Time	t_b		-	12	-	

Notes

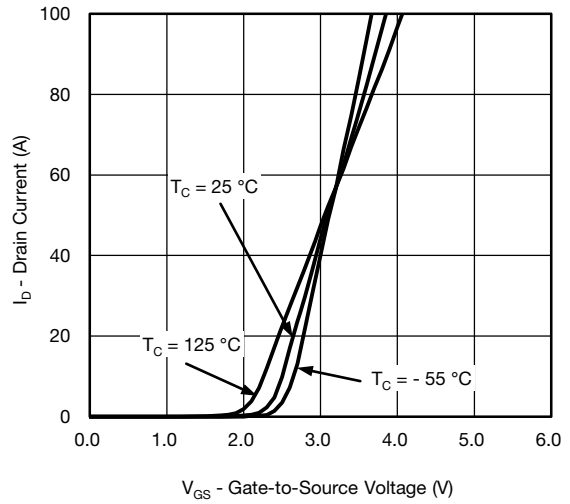
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.
 c. $T_{CASE} = 25\text{ }^\circ\text{C}$. Expected voltage stress during 100% UIS test. Production datalog is not available.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

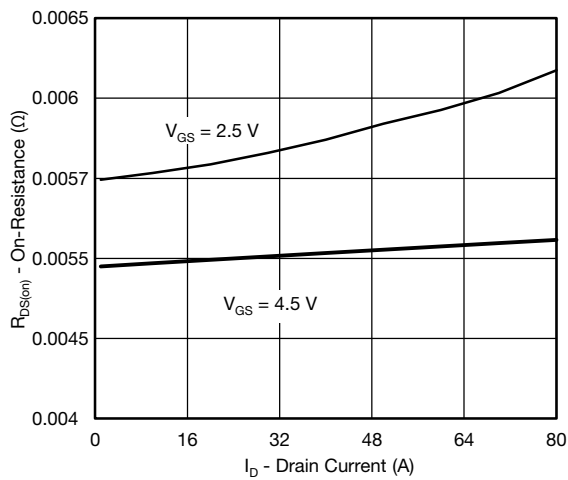
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



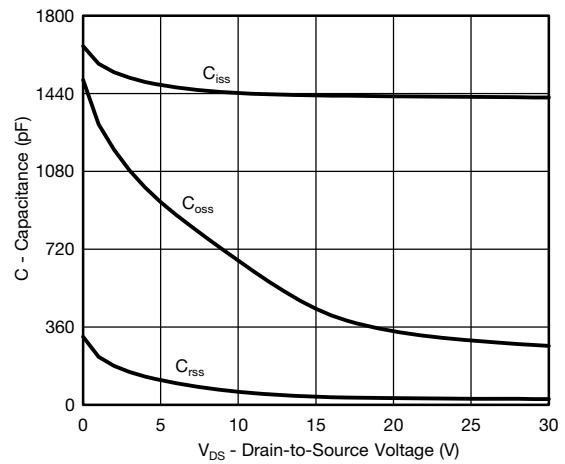
Output Characteristics



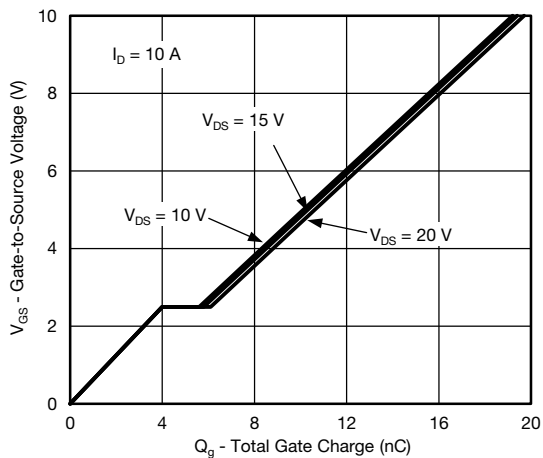
Transfer Characteristics



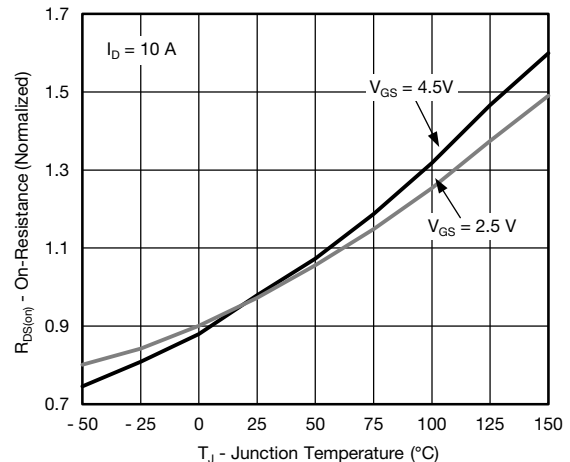
On-Resistance vs. Drain Current



Capacitance

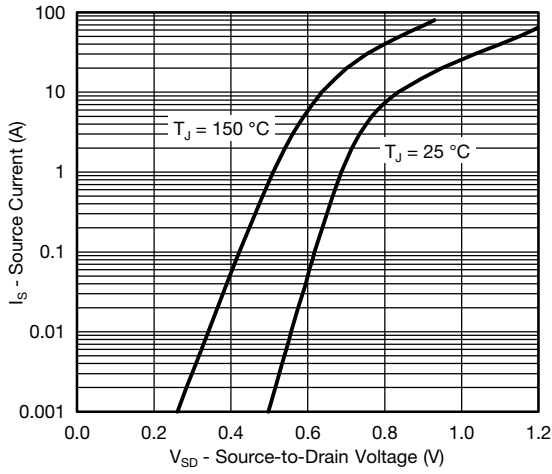


Gate Charge

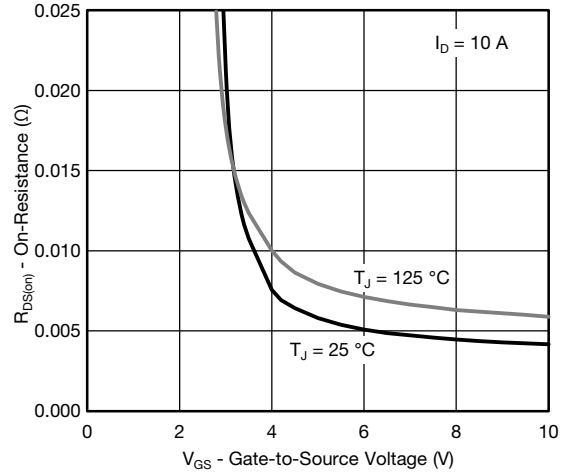


On-Resistance vs. Junction Temperature

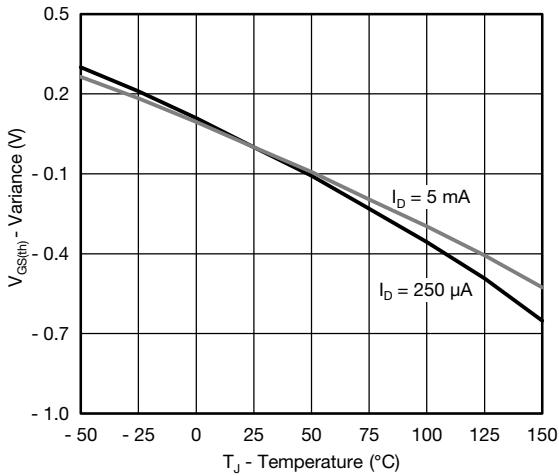
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



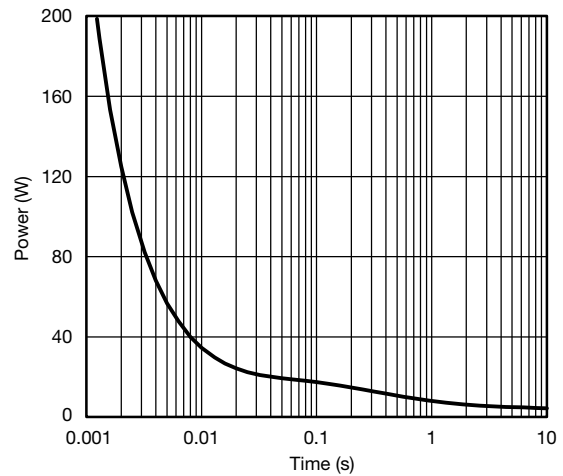
Source-Drain Diode Forward Voltage



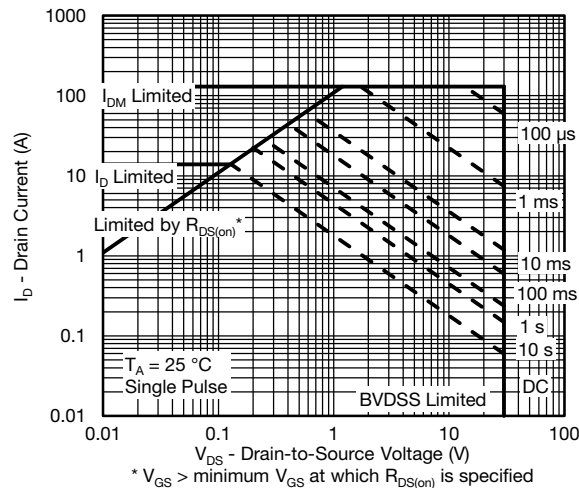
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

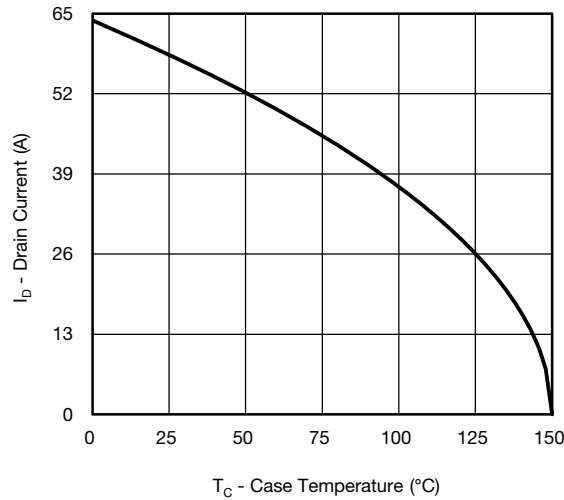


Single Pulse Power, Junction-to-Ambient

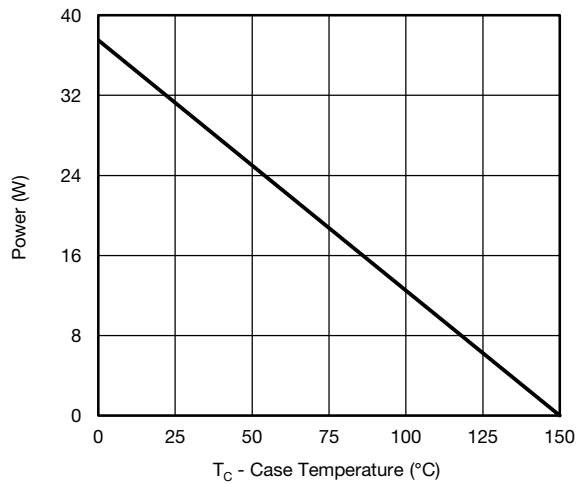


Safe Operating Area

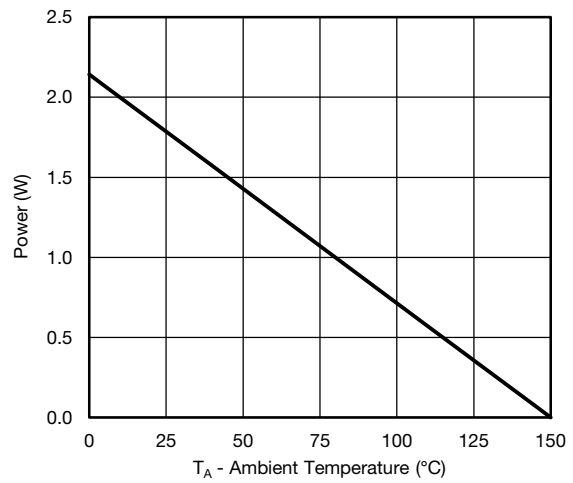
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



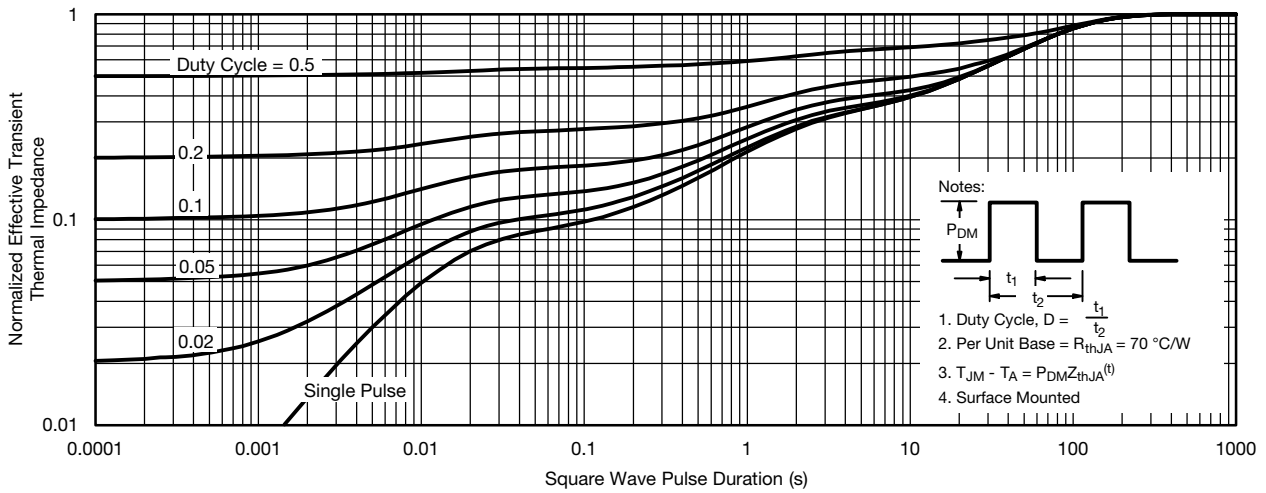
Power, Junction-to-Case



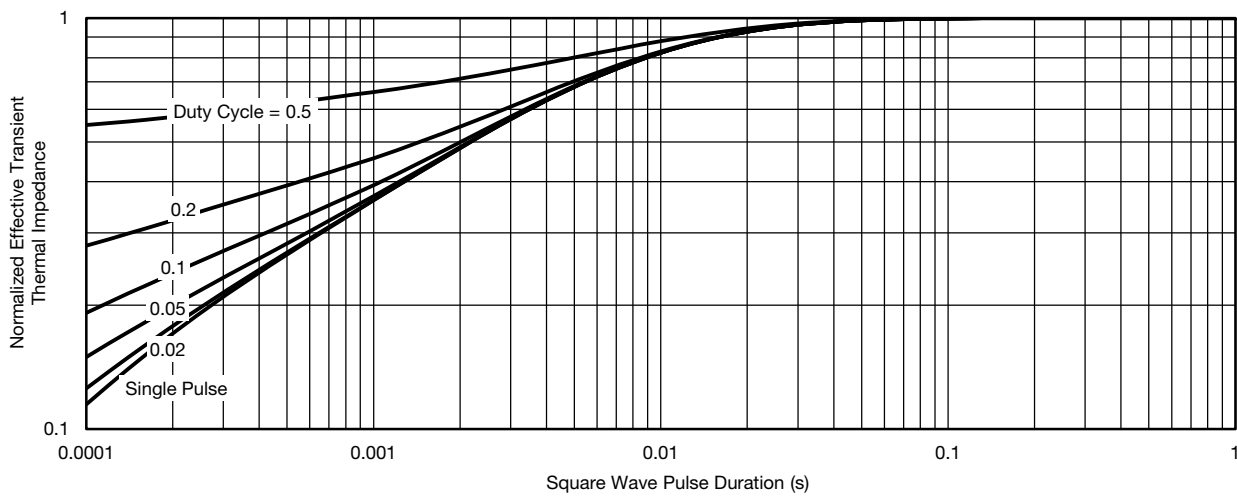
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

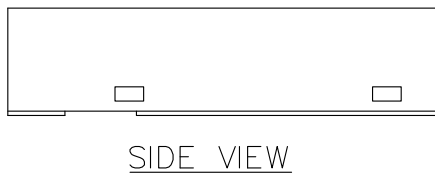
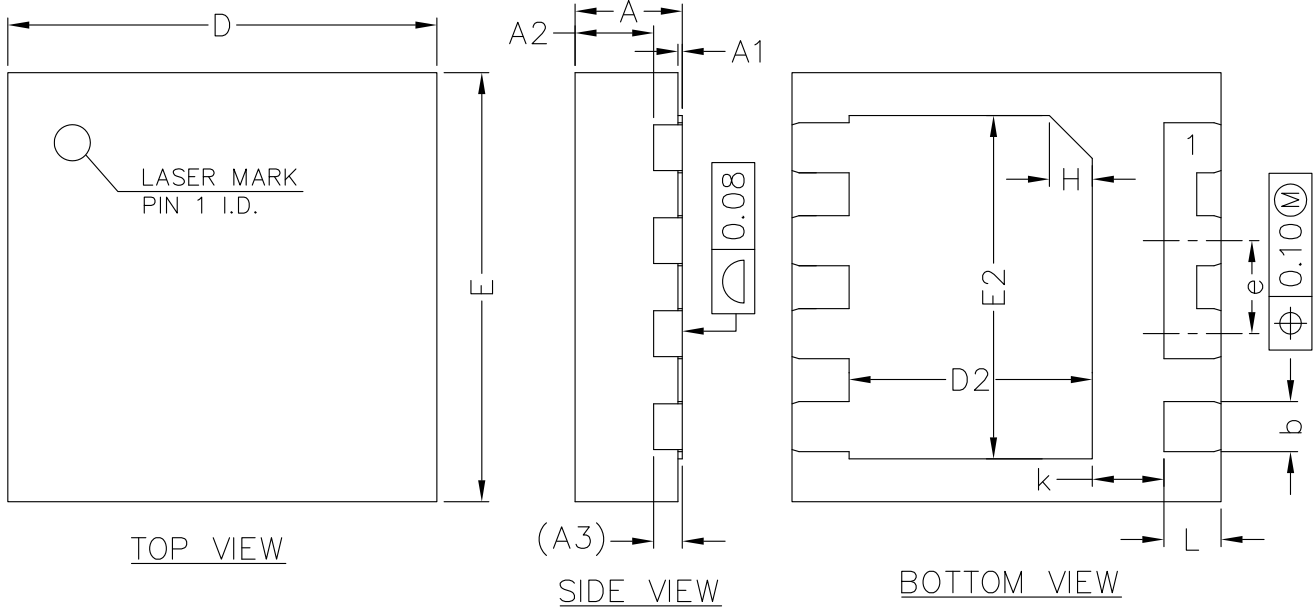
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A2	0.50	0.55	0.60
A3	0.20REF		
b	0.30	0.35	0.40
D	2.90	3.00	3.10
E	2.90	3.00	3.10
D2	1.60	1.70	1.80
E2	2.30	2.40	2.50
e	0.55	0.65	0.75
K	0.40	0.50	0.60
L	0.35	0.40	0.45

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